NPN SILICON HIGH FREQUENCY TRANSISTOR

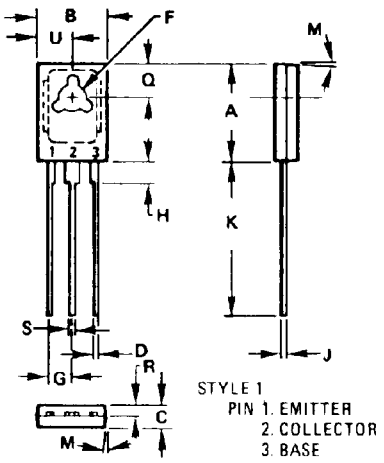
DESCRIPTION:

The **ASI BFT51F.A** is Designed for High Frequency Amplifier Applications.

MAXIMUM RATINGS

I_C	500 mA
V_{CE}	20 V
P_{DISS}	3.0 W @ T_C = 25 °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +175 °C
θ_{JC}	50 °C/W

PACKAGE STYLE TO- 126



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.80	11.05	0.425	0.435
B	7.49	7.75	0.295	0.305
C	2.41	2.67	0.095	0.105
D	0.51	0.66	0.020	0.026
F	2.92	3.00	0.115	0.118
G	2.31	2.46	0.091	0.097
H	2.16	2.41	0.085	0.095
J	0.38	0.64	0.015	0.025
K	15.38	16.64	0.605	0.655
M	3° TYP		3° TYP	
Q	3.76	4.01	0.148	0.158
R	1.14	1.40	0.045	0.055
S	0.64	0.89	0.025	0.035
U	3.68	3.94	0.145	0.155

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 5.0 mA	10			V
BV_{CER}	I_C = 1.0 mA R_{BE} = 100 Ω	18			V
BV_{CBO}	I_C = 1.0 mA	20			V
I_{CEO}	V_{CE} = 5.0 V			1.0	mA
I_{CES}	V_{CE} = 10 V			100	µA
I_{EBO}	V_{EB} = 3.0 V			1.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA I_C = 300 mA	40			---
f_t	V_{CE} = 5.0 V I_C = 300 mA f = 100 MHz	1.0	2.0		GHz
C_{ob}	V_{CB} = 5.0 V f = 1.0 MHz		4.0		pF